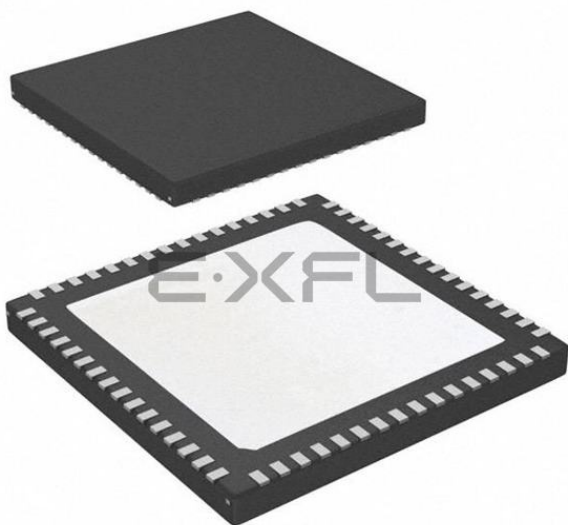




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Details

Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	I ² C, IrDA, SmartCard, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, POR, PWM, WDT
Number of I/O	56
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	128K x 8
Voltage - Supply (Vcc/Vdd)	1.98V ~ 3.8V
Data Converters	A/D 8x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-VFQFN Exposed Pad
Supplier Device Package	64-QFN (9x9)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32gg230f512g-e-qfn64r

3 Electrical Characteristics

3.1 Test Conditions

3.1.1 Typical Values

The typical data are based on $T_{AMB}=25^{\circ}\text{C}$ and $V_{DD}=3.0\text{ V}$, as defined in Table 3.2 (p. 9), unless otherwise specified.

3.1.2 Minimum and Maximum Values

The minimum and maximum values represent the worst conditions of ambient temperature, supply voltage and frequencies, as defined in Table 3.2 (p. 9), unless otherwise specified.

3.2 Absolute Maximum Ratings

The absolute maximum ratings are stress ratings, and functional operation under such conditions are not guaranteed. Stress beyond the limits specified in Table 3.1 (p. 9) may affect the device reliability or cause permanent damage to the device. Functional operating conditions are given in Table 3.2 (p. 9).

Table 3.1. Absolute Maximum Ratings

Symbol	Parameter	Condition	Min	Typ	Max	Unit
T_{STG}	Storage temperature range		-40		150	$^{\circ}\text{C}$
T_S	Maximum soldering temperature	Latest IPC/JEDEC J-STD-020 Standard			260	$^{\circ}\text{C}$
V_{DDMAX}	External main supply voltage		0		3.8	V
V_{IOPIN}	Voltage on any I/O pin		-0.3		$V_{DD}+0.3$	V
I_{IOMAX}	Current per I/O pin (sink)				100	mA
	Current per I/O pin (source)				-100	mA

3.3 General Operating Conditions

3.3.1 General Operating Conditions

Table 3.2. General Operating Conditions

Symbol	Parameter	Min	Typ	Max	Unit
T_{AMB}	Ambient temperature range	-40		85	$^{\circ}\text{C}$
V_{DDOP}	Operating supply voltage	1.98		3.8	V
f_{APB}	Internal APB clock frequency			48	MHz
f_{AHB}	Internal AHB clock frequency			48	MHz

Table 3.5. Power Management

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V _{BODextthr-}	BOD threshold on falling external supply voltage	EM0	1.74		1.96	V
		EM2	1.74		1.98	V
V _{BODintthr-}	BOD threshold on falling internally regulated supply voltage		1.57		1.70	V
V _{BODextthr+}	BOD threshold on rising external supply voltage			1.85	1.98	V
V _{PORthr+}	Power-on Reset (POR) threshold on rising external supply voltage				1.98	V
t _{RESET}	Delay from reset is released until program execution starts	Applies to Power-on Reset, Brown-out Reset and pin reset.		163		μs
C _{DECOUPLE}	Voltage regulator decoupling capacitor.	X5R capacitor recommended. Apply between DECOUPLE pin and GROUND		1		μF

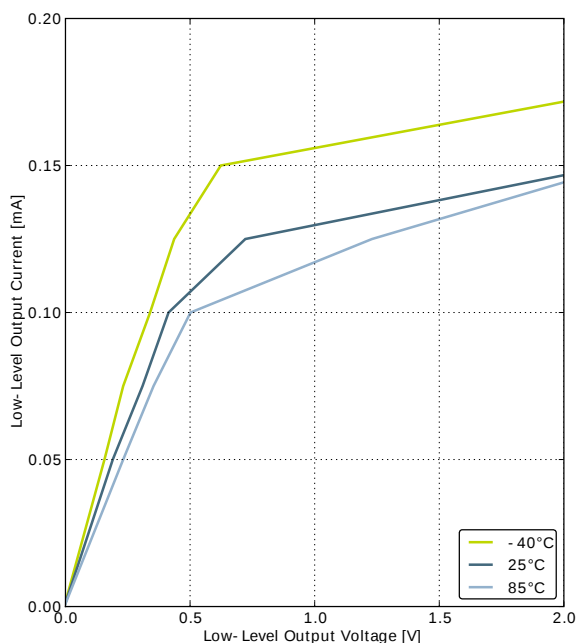
3.7 Flash

Table 3.6. Flash

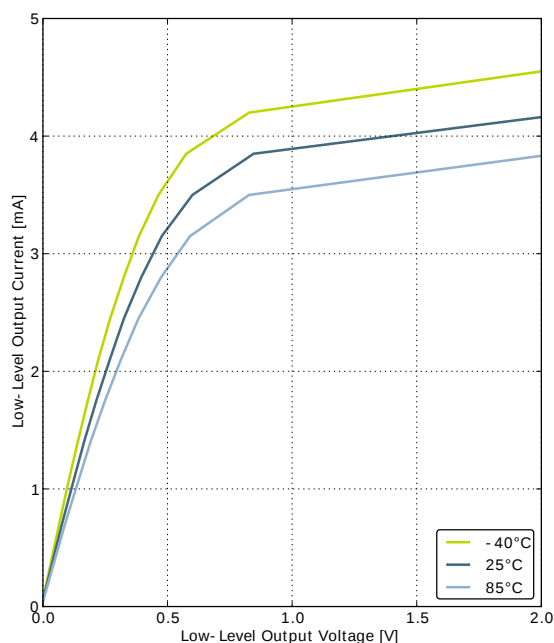
Symbol	Parameter	Condition	Min	Typ	Max	Unit
EC _{FLASH}	Flash erase cycles before failure		20000			cycles
RET _{FLASH}	Flash data retention	T _{AMB} <150°C	10000			h
		T _{AMB} <85°C	10			years
		T _{AMB} <70°C	20			years
t _{W_PROG}	Word (32-bit) programming time		20			μs
t _{PERASE}	Page erase time	LPERASE == 0	20	20.4	20.8	ms
		LPERASE == 1	40	40.4	40.8	ms
t _{DERASE}	Device erase time				161.6	ms
I _{ERASE}	Erase current	LPERASE == 0			14 ¹	mA
		LPERASE == 1			7 ¹	mA
I _{WRITE}	Write current	LPWRITE == 0			14 ¹	mA
		LPWRITE == 1			7 ¹	mA
V _{FLASH}	Supply voltage during flash erase and write		1.98		3.8	V

¹ Measured at 25°C

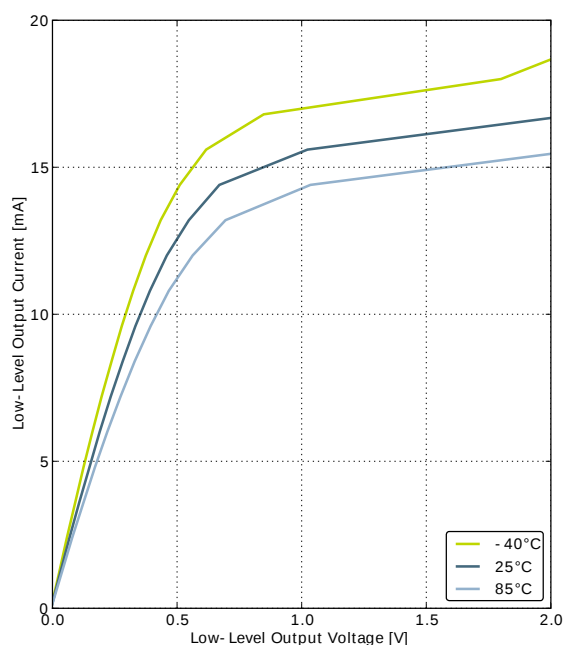
Figure 3.4. Typical Low-Level Output Current, 2V Supply Voltage



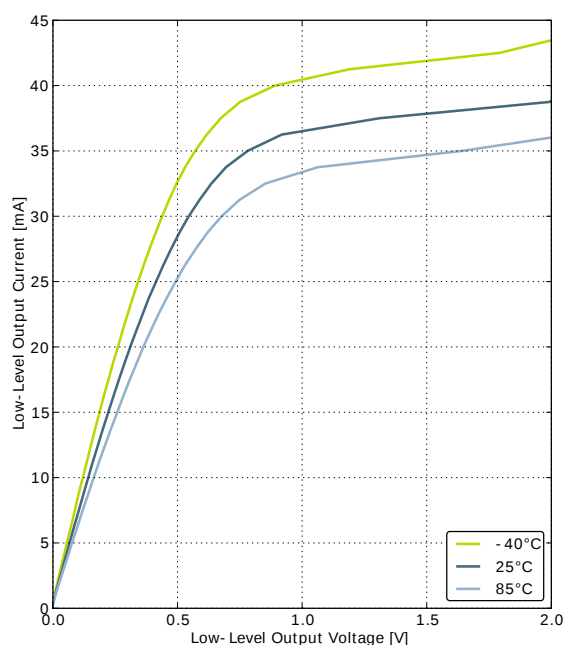
GPIO_Px_CTRL DRIVEMODE = LOWEST



GPIO_Px_CTRL DRIVEMODE = LOW

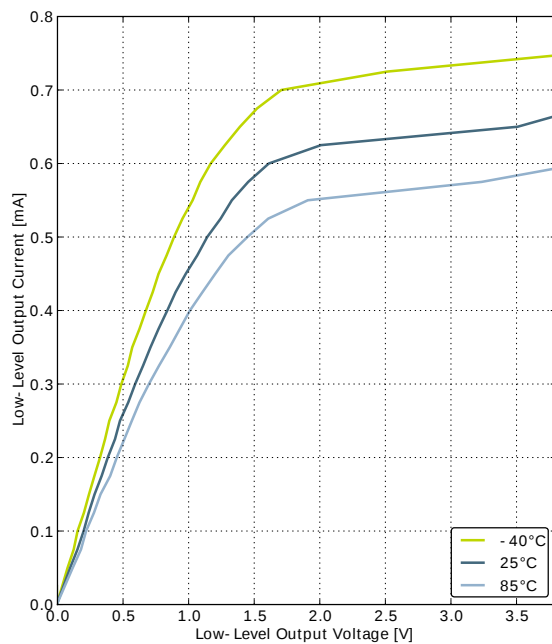


GPIO_Px_CTRL DRIVEMODE = STANDARD

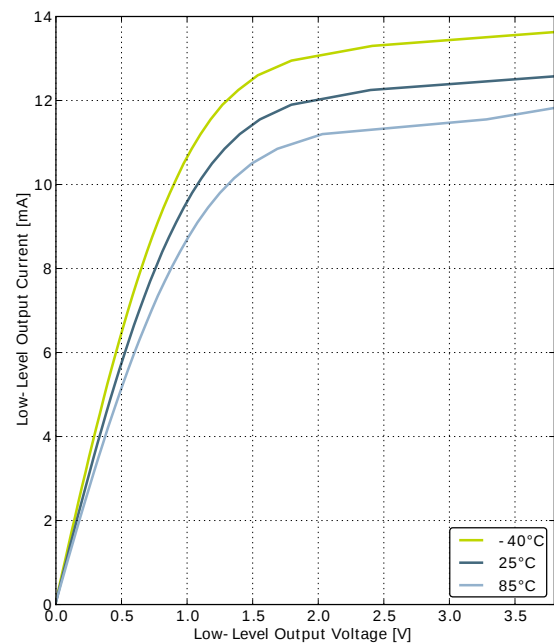


GPIO_Px_CTRL DRIVEMODE = HIGH

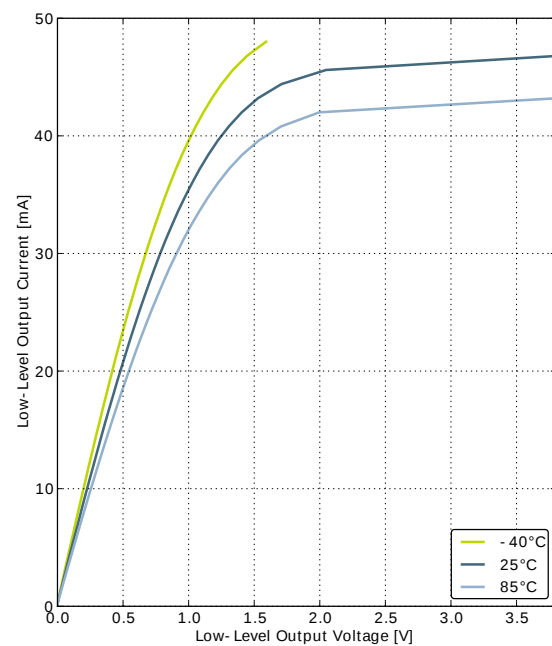
Figure 3.8. Typical Low-Level Output Current, 3.8V Supply Voltage



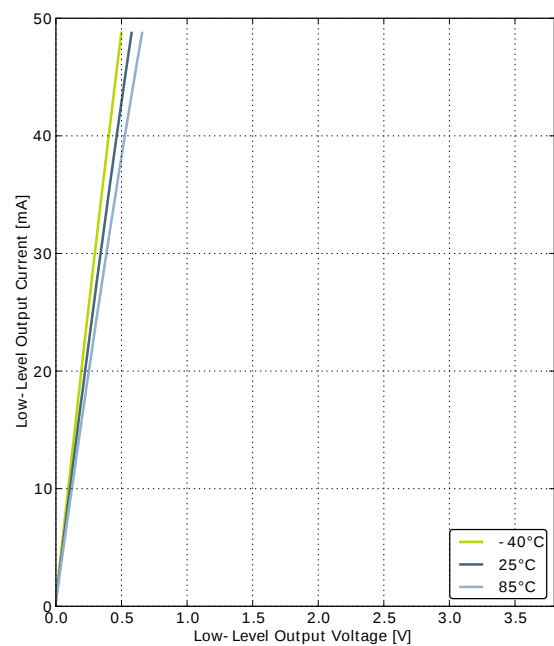
GPIO_Px_CTRL DRIVEMODE = LOWEST



GPIO_Px_CTRL DRIVEMODE = LOW



GPIO_Px_CTRL DRIVEMODE = STANDARD



GPIO_Px_CTRL DRIVEMODE = HIGH

3.9 Oscillators

3.9.1 LFXO

Table 3.8. LFXO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{LFXO}	Supported nominal crystal frequency			32.768		kHz
ESR_{LFXO}	Supported crystal equivalent series resistance (ESR)			30	120	kOhm
C_{LFXOL}	Supported crystal external load range		$\times^1$		25	pF
DC_{LFXO}	Duty cycle		48	50	53.5	%
I_{LFXO}	Current consumption for core and buffer after startup.	ESR=30 kOhm, C_L =10 pF, LFXOBOOST in CMU_CTRL is 1		190		nA
t_{LFXO}	Start- up time.	ESR=30 kOhm, C_L =10 pF, 40% - 60% duty cycle has been reached, LFXOBOOST in CMU_CTRL is 1		400		ms

¹See Minimum Load Capacitance (C_{LFXOL}) Requirement For Safe Crystal Startup in energyAware Designer in Simplicity Studio

For safe startup of a given crystal, the Configurator tool in Simplicity Studio contains a tool to help users configure both load capacitance and software settings for using the LFXO. For details regarding the crystal configuration, the reader is referred to application note "AN0016 EFM32 Oscillator Design Consideration".

3.9.2 HFXO

Table 3.9. HFXO

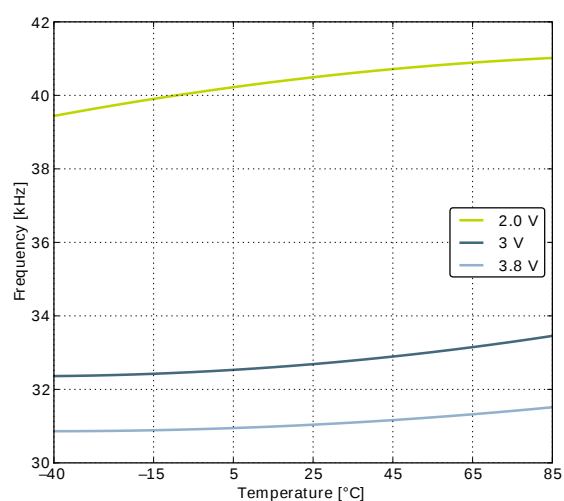
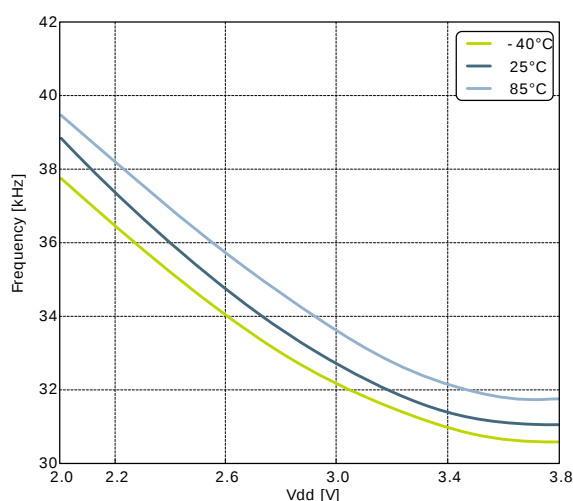
Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{HFXO}	Supported nominal crystal Frequency		4		48	MHz
ESR_{HFXO}	Supported crystal equivalent series resistance (ESR)	Crystal frequency 48 MHz			50	Ohm
		Crystal frequency 32 MHz		30	60	Ohm
		Crystal frequency 4 MHz		400	1500	Ohm
g_{mHFXO}	The transconductance of the HFXO input transistor at crystal startup	HFXOBOOST in CMU_CTRL equals 0b11	20			mS
C_{HFXOL}	Supported crystal external load range		5		25	pF
I_{HFXO}	Current consumption for HFXO after startup	4 MHz: ESR=400 Ohm, C_L =20 pF, HFXOBOOST in CMU_CTRL equals 0b11		85		μ A
		32 MHz: ESR=30 Ohm, C_L =10 pF, HFXOBOOST in CMU_CTRL equals 0b11		165		μ A
t_{HFXO}	Startup time	32 MHz: ESR=30 Ohm, C_L =10 pF, HFXOBOOST in CMU_CTRL equals 0b11		400		μ s

3.9.3 LFRCO

Table 3.10. LFRCO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{LFRCO}	Oscillation frequency, $V_{\text{DD}} = 3.0 \text{ V}$, $T_{\text{AMB}} = 25^\circ\text{C}$		31.29	32.768	34.28	kHz
t_{LFRCO}	Startup time not including software calibration			150		μs
I_{LFRCO}	Current consumption			300	900	nA
$\text{TUNESTEP}_{\text{LFRCO}}$	Frequency step for LSB change in TUNING value			1.5		%

Figure 3.10. Calibrated LFRCO Frequency vs Temperature and Supply Voltage



3.9.4 HFRCO

Table 3.11. HFRCO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{HFRCO}	Oscillation frequency, $V_{\text{DD}} = 3.0 \text{ V}$, $T_{\text{AMB}} = 25^\circ\text{C}$	28 MHz frequency band	27.5	28.0	28.5	MHz
		21 MHz frequency band	20.6	21.0	21.4	MHz
		14 MHz frequency band	13.7	14.0	14.3	MHz
		11 MHz frequency band	10.8	11.0	11.2	MHz
		7 MHz frequency band	6.48 ¹	6.60 ¹	6.72 ¹	MHz
		1 MHz frequency band	1.15 ²	1.20 ²	1.25 ²	MHz
$t_{\text{HFRCO_settling}}$	Settling time after start-up	$f_{\text{HFRCO}} = 14 \text{ MHz}$		0.6		Cycles
	Settling time after band switch			25		Cycles

3.9.6 ULFRCO

Table 3.13. ULFRCO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{ULFRCO}	Oscillation frequency	25°C, 3V	0.70		1.75	kHz
TC_{ULFRCO}	Temperature coefficient			0.05		%/°C
VC_{ULFRCO}	Supply voltage coefficient			-18.2		%/V

3.10 Analog Digital Converter (ADC)

Table 3.14. ADC

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{ADCIN}	Input voltage range	Single ended	0		V_{REF}	V
		Differential	$-V_{REF}/2$		$V_{REF}/2$	V
$V_{ADCREFIN}$	Input range of external reference voltage, single ended and differential		1.25		V_{DD}	V
$V_{ADCREFIN_CH7}$	Input range of external negative reference voltage on channel 7	See $V_{ADCREFIN}$	0		$V_{DD} - 1.1$	V
$V_{ADCREFIN_CH6}$	Input range of external positive reference voltage on channel 6	See $V_{ADCREFIN}$	0.625		V_{DD}	V
$V_{ADCCMIN}$	Common mode input range		0		V_{DD}	V
I_{ADCIN}	Input current	2pF sampling capacitors		<100		nA
$CMRR_{ADC}$	Analog input common mode rejection ratio			65		dB
I_{ADC}	Average active current	1 MSamples/s, 12 bit, external reference		351		μA
		10 kSamples/s 12 bit, internal 1.25 V reference, WARMUP-MODE in ADCn_CTRL set to 0b00		67		μA
		10 kSamples/s 12 bit, internal 1.25 V reference, WARMUP-MODE in ADCn_CTRL set to 0b01		63		μA
		10 kSamples/s 12 bit, internal 1.25 V reference, WARMUP-MODE in ADCn_CTRL set to 0b10		64		μA
I_{ADCREF}	Current consumption of internal voltage reference	Internal voltage reference		65		μA

Symbol	Parameter	Condition	Min	Typ	Max	Unit
C _{ADCIN}	Input capacitance			2		pF
R _{ADCIN}	Input ON resistance		1			MOhm
R _{ADCFLT}	Input RC filter resistance			10		kOhm
C _{ADCFLT}	Input RC filter/de-coupling capacitance			250		fF
f _{ADCCLK}	ADC Clock Frequency				13	MHz
t _{ADCCONV}	Conversion time	6 bit	7			ADC-CLK Cycles
		8 bit	11			ADC-CLK Cycles
		12 bit	13			ADC-CLK Cycles
t _{ADCACQ}	Acquisition time	Programmable	1		256	ADC-CLK Cycles
t _{ADCACQVDD3}	Required acquisition time for VDD/3 reference		2			μs
t _{ADCSTART}	Startup time of reference generator and ADC core in NORMAL mode			5		μs
	Startup time of reference generator and ADC core in KEEPADCWARM mode			1		μs
SNR _{ADC}	Signal to Noise Ratio (SNR)	1 MSamples/s, 12 bit, single ended, internal 1.25V reference		59		dB
		1 MSamples/s, 12 bit, single ended, internal 2.5V reference		63		dB
		1 MSamples/s, 12 bit, single ended, V _{DD} reference		65		dB
		1 MSamples/s, 12 bit, differential, internal 1.25V reference		60		dB
		1 MSamples/s, 12 bit, differential, internal 2.5V reference		65		dB
		1 MSamples/s, 12 bit, differential, 5V reference		54		dB
		1 MSamples/s, 12 bit, differential, V _{DD} reference		67		dB
		1 MSamples/s, 12 bit, differential, 2xV _{DD} reference		69		dB

Figure 3.18. Differential Non-Linearity (DNL)

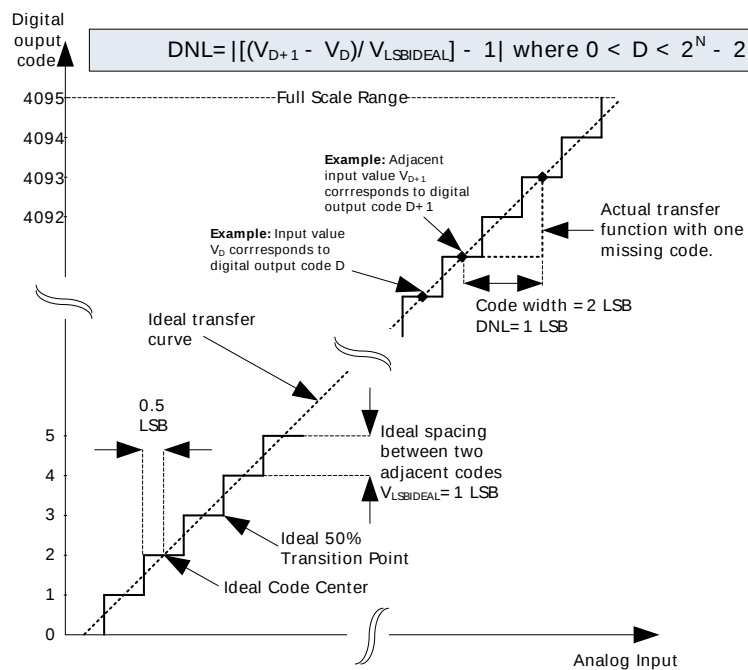
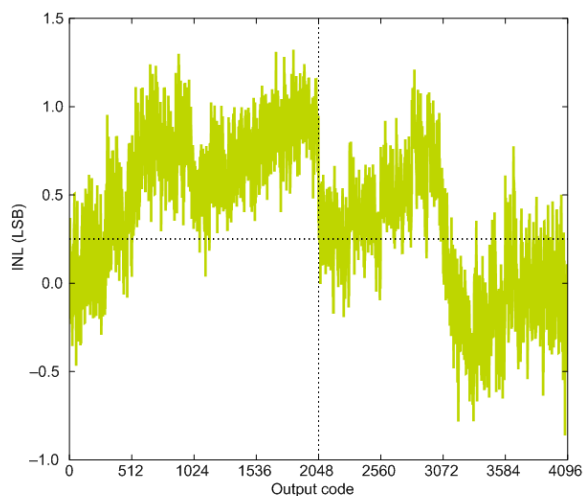
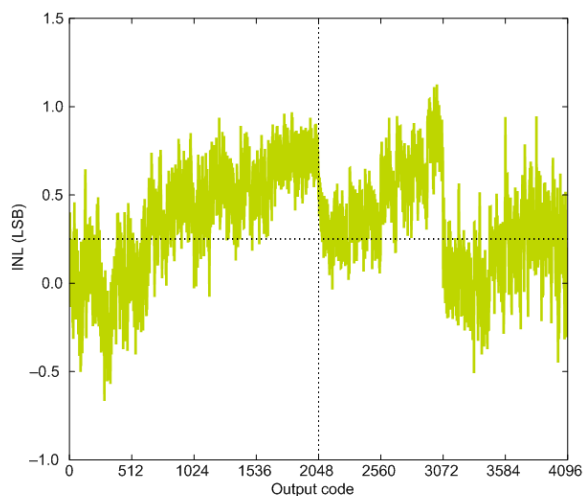
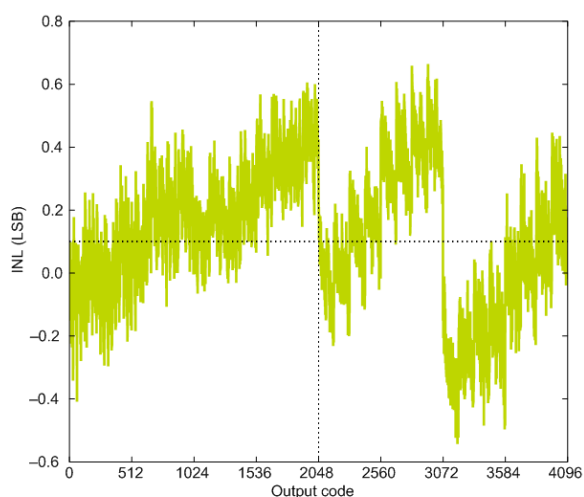
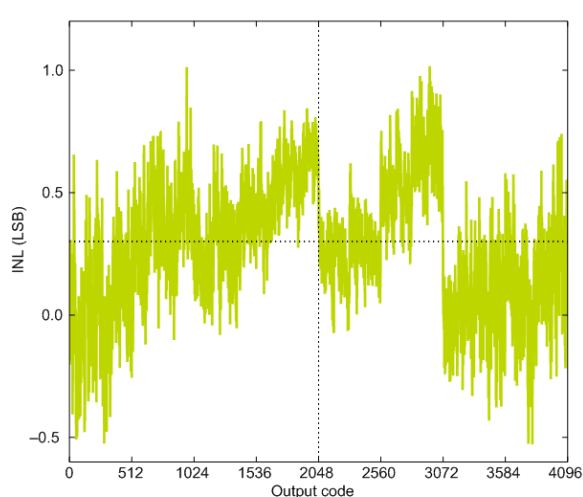
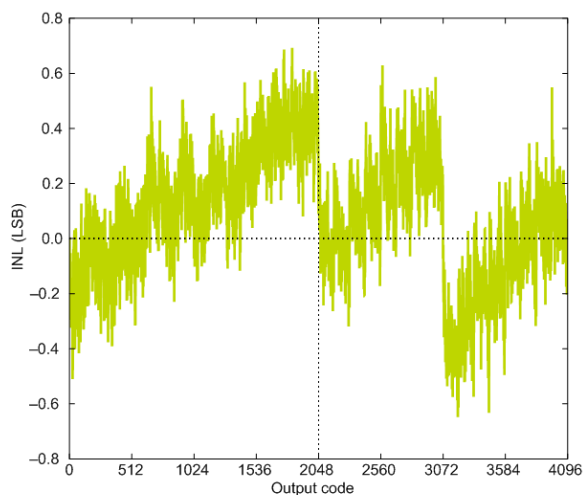


Figure 3.20. ADC Integral Linearity Error vs Code, Vdd = 3V, Temp = 25°C**1.25V Reference****2.5V Reference****2XVDDVSS Reference****5VDIFF Reference****VDD Reference**

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		500 kSamples/s, 12 bit, differential, internal 2.5V reference		58		dB
		500 kSamples/s, 12 bit, differential, V_{DD} reference		59		dB
SNDR _{DAC}	Signal to Noise-pulse Distortion Ratio (SNDR)	500 kSamples/s, 12 bit, single ended, internal 1.25V reference		57		dB
		500 kSamples/s, 12 bit, single ended, internal 2.5V reference		54		dB
		500 kSamples/s, 12 bit, differential, internal 1.25V reference		56		dB
		500 kSamples/s, 12 bit, differential, internal 2.5V reference		53		dB
		500 kSamples/s, 12 bit, differential, V_{DD} reference		55		dB
SFDR _{DAC}	Spurious-Free Dynamic Range(SFDR)	500 kSamples/s, 12 bit, single ended, internal 1.25V reference		62		dBc
		500 kSamples/s, 12 bit, single ended, internal 2.5V reference		56		dBc
		500 kSamples/s, 12 bit, differential, internal 1.25V reference		61		dBc
		500 kSamples/s, 12 bit, differential, internal 2.5V reference		55		dBc
		500 kSamples/s, 12 bit, differential, V_{DD} reference		60		dBc
V _{DACOFFSET}	Offset voltage	After calibration, single ended		2	12	mV
		After calibration, differential		2		mV
DNL _{DAC}	Differential non-linearity			±1		LSB
INL _{DAC}	Integral non-linearity			±5		LSB
MC _{DAC}	No missing codes			12		bits

¹ Measured with a static input code and no loading on the output.

3.12 Operational Amplifier (OPAMP)

The electrical characteristics for the Operational Amplifiers are based on simulations.

Table 3.16. OPAMP

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I _{OPAMP}	Active Current	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0, Unity Gain		350	405	μA
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1, Unity Gain		95	115	μA

3.13 Analog Comparator (ACMP)

Table 3.17. ACMP

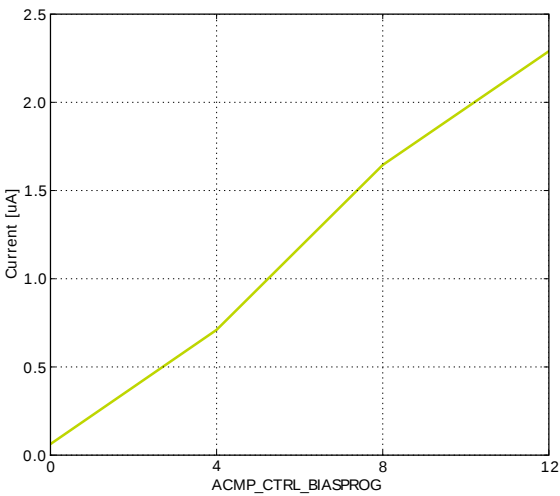
Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{ACMPIN}	Input voltage range		0		V_{DD}	V
V_{ACMPCM}	ACMP Common Mode voltage range		0		V_{DD}	V
I_{ACMP}	Active current	BIASPROG=0b0000, FULL-BIAS=0 and HALFBIAS=1 in ACMPn_CTRL register		0.1	0.6	μA
		BIASPROG=0b1111, FULL-BIAS=0 and HALFBIAS=0 in ACMPn_CTRL register		2.87	12	μA
		BIASPROG=0b1111, FULL-BIAS=1 and HALFBIAS=0 in ACMPn_CTRL register		250	520	μA
$I_{ACMPREF}$	Current consumption of internal voltage reference	Internal voltage reference off. Using external voltage reference		0		μA
		Internal voltage reference		5		μA
$V_{ACMPOFFSET}$	Offset voltage	BIASPROG= 0b1010, FULL-BIAS=0 and HALFBIAS=0 in ACMPn_CTRL register	-12	0	12	mV
$V_{ACMPHYST}$	ACMP hysteresis	Programmable		17		mV
R_{CSRES}	Capacitive Sense Internal Resistance	CSRESSEL=0b00 in ACMPn_INPUTSEL		43		kOhm
		CSRESSEL=0b01 in ACMPn_INPUTSEL		78		kOhm
		CSRESSEL=0b10 in ACMPn_INPUTSEL		111		kOhm
		CSRESSEL=0b11 in ACMPn_INPUTSEL		145		kOhm
$t_{ACMPSTART}$	Startup time				10	μs

The total ACMP current is the sum of the contributions from the ACMP and its internal voltage reference as given in Equation 3.1 (p. 42) . $I_{ACMPREF}$ is zero if an external voltage reference is used.

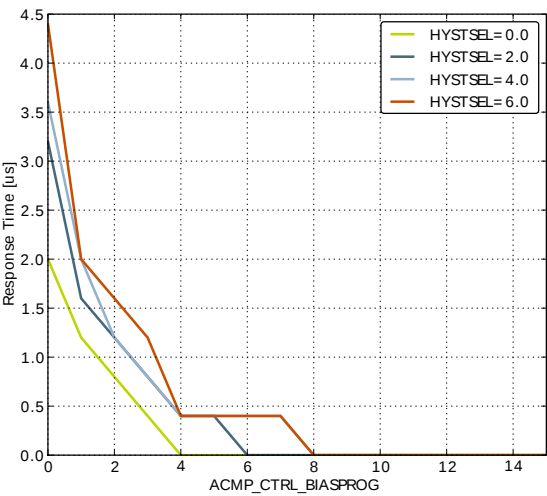
Total ACMP Active Current

$$I_{ACMPTOTAL} = I_{ACMP} + I_{ACMPREF} \quad (3.1)$$

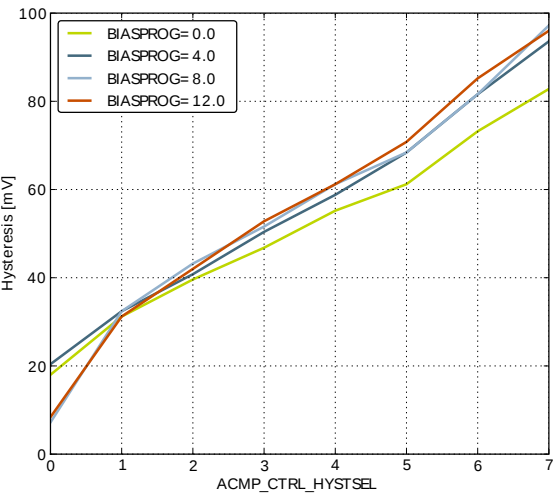
Figure 3.30. ACMP Characteristics, Vdd = 3V, Temp = 25°C, FULLBIAS = 0, HALFBIAS = 1



Current consumption, HYSTSEL = 4



Response time



Hysteresis

Table 3.20. I2C Fast-mode (Fm)

Symbol	Parameter	Min	Typ	Max	Unit
f _{SCL}	SCL clock frequency	0		400 ¹	kHz
t _{LOW}	SCL clock low time	1.3			μs
t _{HIGH}	SCL clock high time	0.6			μs
t _{SU,DAT}	SDA set-up time	100			ns
t _{HD,DAT}	SDA hold time	8		900 ^{2,3}	ns
t _{SU,STA}	Repeated START condition set-up time	0.6			μs
t _{HD,STA}	(Repeated) START condition hold time	0.6			μs
t _{SU,STO}	STOP condition set-up time	0.6			μs
t _{BUF}	Bus free time between a STOP and START condition	1.3			μs

¹For the minimum HPERCLK frequency required in Fast-mode, see the I2C chapter in the EFM32GG Reference Manual.

²The maximum SDA hold time (t_{HD,DAT}) needs to be met only when the device does not stretch the low time of SCL (t_{LOW}).

³When transmitting data, this number is guaranteed only when $I2Cn_CLKDIV < ((900 \cdot 10^{-9} [s] \cdot f_{HPERCLK} [Hz]) - 4)$.

Table 3.21. I2C Fast-mode Plus (Fm+)

Symbol	Parameter	Min	Typ	Max	Unit
f _{SCL}	SCL clock frequency	0		1000 ¹	kHz
t _{LOW}	SCL clock low time	0.5			μs
t _{HIGH}	SCL clock high time	0.26			μs
t _{SU,DAT}	SDA set-up time	50			ns
t _{HD,DAT}	SDA hold time	8			ns
t _{SU,STA}	Repeated START condition set-up time	0.26			μs
t _{HD,STA}	(Repeated) START condition hold time	0.26			μs
t _{SU,STO}	STOP condition set-up time	0.26			μs
t _{BUF}	Bus free time between a STOP and START condition	0.5			μs

¹For the minimum HPERCLK frequency required in Fast-mode Plus, see the I2C chapter in the EFM32GG Reference Manual.

3.16 USART SPI

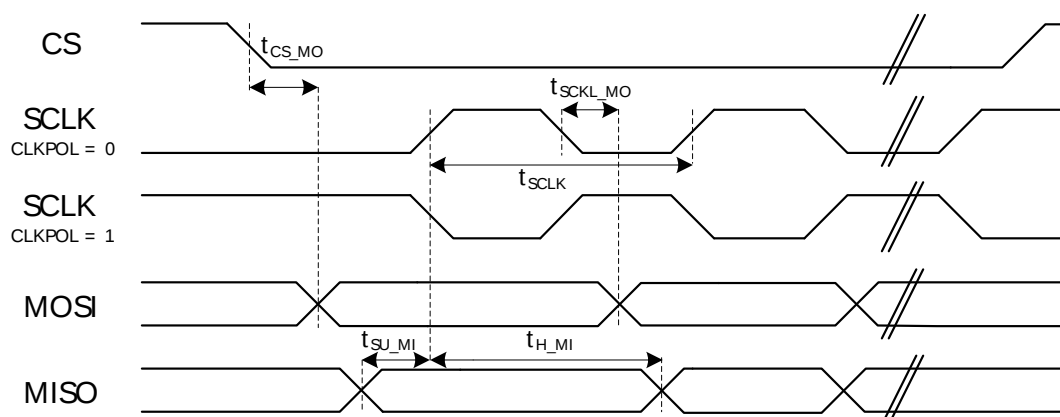
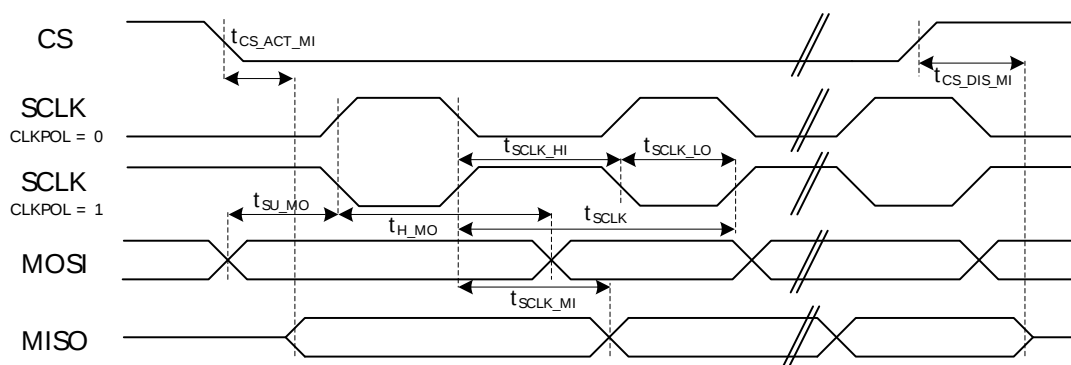
Figure 3.31. SPI Master Timing

Table 3.22. SPI Master Timing

Symbol	Parameter	Condition	Min	Typ	Max	Unit
$t_{\text{SCLK}}^{1,2}$	SCLK period		$2 * t_{\text{HFER-CLK}}$			ns
$t_{\text{CS_MO}}^{1,2}$	CS to MOSI		-2.00		1.00	ns
$t_{\text{SCLK_MO}}^{1,2}$	SCLK to MOSI		-4.00		3.00	ns
$t_{\text{SU_MI}}^{1,2}$	MISO setup time	IOVDD = 1.98 V	36.00			ns
		IOVDD = 3.0 V	29.00			ns
$t_{\text{H_MI}}^{1,2}$	MISO hold time		-4.00			ns

¹Applies for both CLKPHA = 0 and CLKPHA = 1 (figure only shows CLKPHA = 0)

²Measurement done at 10% and 90% of V_{DD} (figure shows 50% of V_{DD})

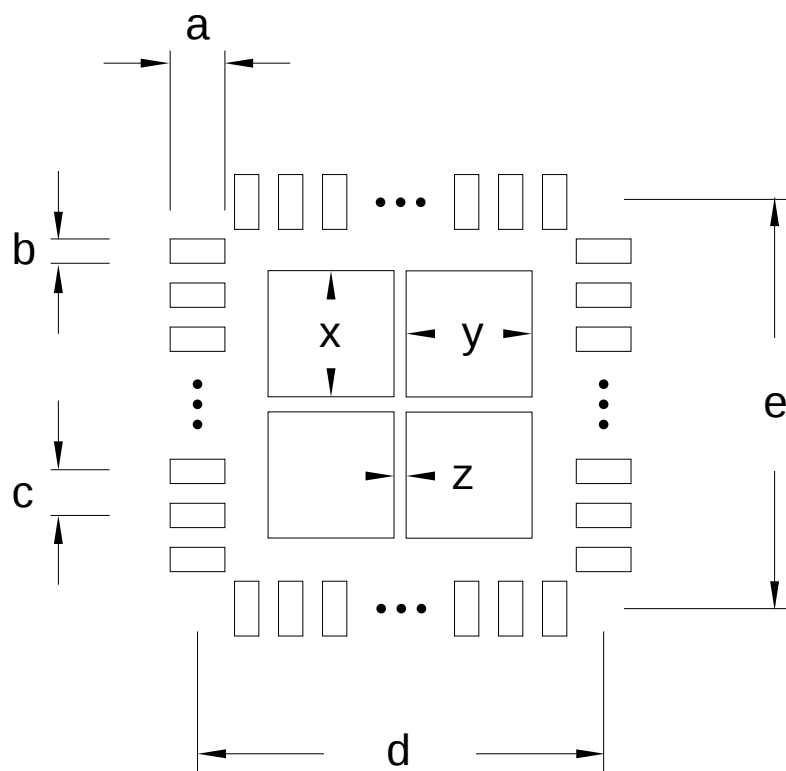
Figure 3.32. SPI Slave Timing**Table 3.23. SPI Slave Timing**

Symbol	Parameter	Min	Typ	Max	Unit
$t_{\text{SCLK_sl}}^{1,2}$	SCKL period	$2 * t_{\text{HFER-CLK}}$			ns
$t_{\text{SCLK_hi}}^{1,2}$	SCLK high period	$3 * t_{\text{HFER-CLK}}$			ns
$t_{\text{SCLK_lo}}^{1,2}$	SCLK low period	$3 * t_{\text{HFER-CLK}}$			ns
$t_{\text{CS_ACT_MI}}^{1,2}$	CS active to MISO	4.00		30.00	ns
$t_{\text{CS_DIS_MI}}^{1,2}$	CS disable to MISO	4.00		30.00	ns
$t_{\text{SU_MO}}^{1,2}$	MOSI setup time	4.00			ns
$t_{\text{H_MO}}^{1,2}$	MOSI hold time	$2 + 2 * t_{\text{HFER-CLK}}$			ns
$t_{\text{SCLK_MI}}^{1,2}$	SCLK to MISO	$9 + t_{\text{HFER-CLK}}$		$36 + 2 * t_{\text{HFER-CLK}}$	ns

¹Applies for both CLKPHA = 0 and CLKPHA = 1 (figure only shows CLKPHA = 0)

²Measurement done at 10% and 90% of V_{DD} (figure shows 50% of V_{DD})

QFN64 Pin# and Name		Pin Alternate Functionality / Description			
Pin #	Pin Name	Analog	Timers	Communication	Other
29	PD1	ADC0_CH1 DAC0_OUT1ALT #4/ OPAMP_OUT1ALT	TIM0_CC0 #3 PCNT2_S1IN #0	US1_RX #1	DBG_SWO #2
30	PD2	ADC0_CH2	TIM0_CC1 #3	US1_CLK #1	DBG_SWO #3
31	PD3	ADC0_CH3 OPAMP_N2	TIM0_CC2 #3	US1_CS #1	ETM_TD1 #0/2
32	PD4	ADC0_CH4 OPAMP_P2		LEU0_TX #0	ETM_TD2 #0/2
33	PD5	ADC0_CH5 OPAMP_OUT2 #0		LEU0_RX #0	ETM_TD3 #0/2
34	PD6	ADC0_CH6 OPAMP_P1	LETIM0_OUT0 #0 TIM1_CC0 #4 PCNT0_S0IN #3	US1_RX #2 I2C0_SDA #1	LES_ALTEX0 #0 ACMP0_O #2 ETM_TD0 #0
35	PD7	ADC0_CH7 OPAMP_N1	LETIM0_OUT1 #0 TIM1_CC1 #4 PCNT0_S1IN #3	US1_TX #2 I2C0_SCL #1	CMU_CLK0 #2 LES_ALTEX1 #0 ACMP1_O #2 ETM_TCLK #0
36	PD8	BU_VIN			CMU_CLK1 #1
37	PC6	ACMP0_CH6		I2C0_SDA #2 LEU1_TX #0	LES_CH6 #0 ETM_TCLK #2
38	PC7	ACMP0_CH7		I2C0_SCL #2 LEU1_RX #0	LES_CH7 #0 ETM_TD0 #2
39	VDD_DREG	Power supply for on-chip voltage regulator.			
40	DECOUPLE	Decouple output for on-chip voltage regulator. An external capacitance of size C _{DECOUPLE} is required at this pin.			
41	PC8	ACMP1_CH0	TIM2_CC0 #2	US0_CS #2	LES_CH8 #0
42	PC9	ACMP1_CH1	TIM2_CC1 #2	US0_CLK #2	LES_CH9 #0 GPIO_EM4WU2
43	PC10	ACMP1_CH2	TIM2_CC2 #2	US0_RX #2	LES_CH10 #0
44	PC11	ACMP1_CH3		US0_TX #2	LES_CH11 #0
45	PC12	ACMP1_CH4 DAC0_OUT1ALT #0/ OPAMP_OUT1ALT			CMU_CLK0 #1 LES_CH12 #0
46	PC13	ACMP1_CH5 DAC0_OUT1ALT #1/ OPAMP_OUT1ALT	TIM0_CDTI0 #1/3 TIM1_CC0 #0 TIM1_CC2 #4 PCNT0_S0IN #0		LES_CH13 #0
47	PC14	ACMP1_CH6 DAC0_OUT1ALT #2/ OPAMP_OUT1ALT	TIM0_CDTI1 #1/3 TIM1_CC1 #0 PCNT0_S1IN #0	US0_CS #3	LES_CH14 #0
48	PC15	ACMP1_CH7 DAC0_OUT1ALT #3/ OPAMP_OUT1ALT	TIM0_CDTI2 #1/3 TIM1_CC2 #0	US0_CLK #3	LES_CH15 #0 DBG_SWO #1
49	PF0		TIM0_CC0 #5 LETIM0_OUT0 #2	US1_CLK #2 I2C0_SDA #5 LEU0_TX #3	DBG_SWCLK #0/1/2/3
50	PF1		TIM0_CC1 #5 LETIM0_OUT1 #2	US1_CS #2 I2C0_SCL #5 LEU0_RX #3	DBG_SWDIO #0/1/2/3 GPIO_EM4WU3
51	PF2		TIM0_CC2 #5	LEU0_TX #4	ACMP1_O #0 DBG_SWO #0 GPIO_EM4WU4
52	PF3		TIM0_CDTI0 #2/5		PRS_CH0 #1 ETM_TD3 #1

Figure 5.3. QFN64 PCB Stencil Design**Table 5.3. QFN64 PCB Stencil Design Dimensions (Dimensions in mm)**

Symbol	Dim. (mm)	Symbol	Dim. (mm)
a	0.75	e	8.90
b	0.22	x	2.70
c	0.50	y	2.70
d	8.90	z	0.80

1. The drawings are not to scale.
2. All dimensions are in millimeters.
3. All drawings are subject to change without notice.
4. The PCB Land Pattern drawing is in compliance with IPC-7351B.
5. Stencil thickness 0.125 mm.
6. For detailed pin-positioning, see Figure 4.3 (p. 56) .

5.2 Soldering Information

The latest IPC/JEDEC J-STD-020 recommendations for Pb-Free reflow soldering should be followed.

Place as many and as small as possible vias underneath each of the solder patches under the ground pad.

7 Revision History

7.1 Revision 1.40

March 21st, 2016

Added clarification on conditions for INL_{ADC} and DNL_{ADC} parameters.

Reduced maximum and typical current consumption for all EM0 entries except 48 MHz in the Current Consumption table in the Electrical Characteristics section.

Increased maximum specifications for EM2 current, EM3 current, and EM4 current in the Current Consumption table in the Electrical Characteristics section.

Increased typical specification for EM2 and EM3 current at 85 C in the Current Consumption table in the Electrical Characteristics section.

Added EM2, EM3, and EM4 current consumption vs. temperature graphs.

Added a new EM2 entry and specified the existing specification is for EM0 for the BOD threshold on falling external supply voltage in the Power Management table in the Electrical Characteristics section.

Reduced maximum input leakage current in the GPIO table in the Electrical Characteristics section.

Added a maximum current consumption specification to the LFRCO table in the Electrical Characteristics section.

Added maximum specifications for the active current including references for two channels to the DAC table in the Electrical Characteristics section.

Increased the maximum specification for DAC offset voltage in the DAC table in the Electrical Characteristics section.

Increased the typical specifications for active current with $FULLBIAS=1$ and capacitive sense internal resistance in the ACMP table in the Electrical Characteristics section.

Added minimum and maximum specifications and updated the typical value for the VCMP offset voltage in the VCMP table in the Electrical Characteristics section.

Removed the maximum specification and reduced the typical value for hysteresis in the VCMP table in the Electrical Characteristics section.

Updated all graphs in the Electrical Characteristics section to display data for 2.0 V as the minimum voltage.

7.2 Revision 1.30

May 23rd, 2014

Removed "preliminary" markings

Updated HFRCO figures.

Corrected single power supply voltage minimum value from 1.85V to 1.98V.

Updated Current Consumption information.

Updated Power Management information.

Updated power requirements in the Power Management section.

Removed minimum load capacitance figure and table. Added reference to application note.

Other minor corrections.

7.6 Revision 1.00

September 11th, 2012

Updated the HFRCO 1 MHz band typical value to 1.2 MHz.

Updated the HFRCO 7 MHz band typical value to 6.6 MHz.

Other minor corrections.

7.7 Revision 0.98

May 25th, 2012

Corrected EM3 current consumption in the Electrical Characteristics section.

7.8 Revision 0.96

February 28th, 2012

Added reference to errata document.

Corrected QFN64 package drawing.

Updated PCB land pattern, solder mask and stencil design.

7.9 Revision 0.95

September 28th, 2011

Flash configuration for Giant Gecko is now 1024KB or 512KB. For flash sizes below 512KB, see the Leopard Gecko Family.

Corrected operating voltage from 1.8 V to 1.85 V.

Added rising POR level to Electrical Characteristics section.

Updated Minimum Load Capacitance (C_{LFXOL}) Requirement For Safe Crystal Startup.

Added Gain error drift and Offset error drift to ADC table.

Added Opamp pinout overview.

Added reference to errata document.

Corrected QFN64 package drawing.

Updated PCB land pattern, solder mask and stencil design.

7.10 Revision 0.91

March 21th, 2011

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